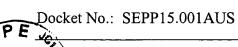
THE CHINE



INFORMATION DISCLOSURE STATEMENT

Applicant

Skarp et al.

Appl. No.

10/003,749

Filed

: October 23, 2001

For

PROCESS FOR PRODUCING

ALUMINUM OXIDE FILMS AT LOW

TEMPERATURES

Examiner

Bret P. Chen

Group Art Unit

1762

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Dear Sir:

Enclosed is form PTO-1449 listing 7 references that are also enclosed. This Information Disclosure Statement is being filed under 37 C.F.R. § 1.97(c)(2) before the mailing date of a final action and before the mailing of a Notice of Allowance. This Statement is accompanied by the fees set forth in 37 C.F.R. § 1.17(p). The Commissioner is hereby authorized to charge any additional fees which may be required or to credit any overpayment to Account No. 11-1410.

By:

Respectfully submitted,

KNOBBE, MARTENS, OLSON & BEAR, LLP

Dated: October 22, 2003

Andrew N. Merickel Registration No. 53,317 Attorney of Record Customer No. 20,995

(415) 054 411 4

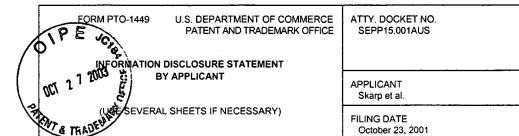
(415) 954-4114

W:\DOCS\ANM\ANM-6023.DOC 101503

10/29/2003 ZJUHAR1 00000055 10003749

02 FC:1806

180.00 OP



		SIIEET TOF I
ATTY, DOCKET NO. SEPP15,001AUS	APPLICATION NO. 10/003,749	
APPLICANT Skarp et al.		
FILING DATE	GROUP	

				U.S. PATENT DOCUMENTS				
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING (IF APPRO	
	1	US 2003/0129298 A1	07/10/03	Tera et al.	2			
	2	US 2001/0031379 A1	10/18/01	Tera et al.	2, C			
	3	US 2002/0003403 A1	01/10/02	Ghosh et al.	13/1			
	4	US 2001/0052752 A1	12/20/01	Ghosh et al.	1000			
				FOREIGN PATENT DOCUMENTS	0			
EXAMINER		DOCUMENT NUMBER	DATE	COUNTRY CLAS		SUBCLASS	TRANSI	_ATION
INITIAL							YES	NO
	5	WO 03/008110 A1	01/30/03	PCT				

* EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)				
	6	Kukli et al, "Atomic layer epitaxy growth of aluminum oxide thin films from a novel Al(CH3)2Cl precursor and H2O.", J. Vac. Sci. Technol. A 15(4), July/Aug 1997, pp. 2214-2218			
	7	Hiltunen et al. "Growth and Characterization of Aluminum Oxide Thin Films Deposited from Various Source Materials by Atomic Layer Epitaxy and Chemical Vapor Deposition Processes", Materials Chemistry and Physics, 28 (1991) pp. 379-388			
•	8				
	9				
	10				

W:\DOCS\ANM\ANM-6024.DOC 101503

EXA	A AI	INIC	==
	IVII	IN	=r